





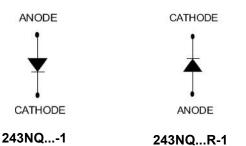
243NQ080/R-1 243NQ100/R-1 SCHOTTKY RECTIFIER



Features

- 175℃ T_J operation
- Unique high power, Half-Pak module
- Replaces three parallel DO-5' S
- Easier to mount and lower profile than DO-5' S
- High purity, high temperature epoxy encapsulation for enhanced
- · mechanical strength and moisture resistance
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.		Units
Peak Repetitive Reverse Voltage	V _{RRM}	-	80	243NQ080-1	.,
Working Peak Reverse Voltage DC Blocking Voltage	$egin{array}{c} egin{array}{c} \egin{array}{c} \egin{array}{c} \egin{array}{c} \egin{array}{c} \egin{array}{c} \egin{array}$		100	243NQ100-1	V
Average Forward Current	I _{F(AV)}	50% duty cycle @T _C =120°C, rectangular wave form		240	А
Peak One Cycle Non-Repetitive Surge Current	I _{FSM}	8.3 ms, half Sine pulse	3960		Α
Non-Repetitive Avalanche Energy	E _{AS}	T _J =25℃,I _{AS} =1A,L=30 mH		15	mJ
Repetitive Avalanche Current	I _{AR}	Current decaying linearly to zero in 1 µsec Frequency limited by T_J max. V_A =1.5× V_R typical	1		А

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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop*	\/	@ 240A, Pulse, T _J = 25 °C	0.80	0.86	V
	V _{F1}	@ 480A, Pulse, T _J = 25 °C	-	1.01	\ \ \
	\/	@ 240A, Pulse, T _J = 125 °C	0.65	0.72	V
	V_{F2}	@ 480A, Pulse, T _J = 125 °C	-	0.86	V
Reverse Current*	I _{R1}	@V _R = rated V _R T _J = 25 °C	0.002	6	mA
	I _{R2}	@V _R = rated V _R T _J = 125 °C	2	80	mA
Junction Capacitance	Ст	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	4800	5500	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

 $^{^{\}star}\,$ Pulse width < 300 $\mu s,\,$ duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specific	Units	
Junction Temperature	TJ	-	-55 to +175		°C
Storage Temperature	T _{stg}	-	-55 to +175		°C
Typical Thermal Resistance Junction to Case	$R_{ heta JC}$	DC operation	0.20		°C/W
Typical Thermal Resistance, case to Heat Sink	$R_{ heta cs}$	Mounting surface, smooth and greased	0.15		°C/W
Mounting Torque	T _M	Non-lubricated threads	Mounting Torque Terminal Torque	23(min) 29(max) 35(min) 46(max)	Kg-cm
Approximate Weight	wt	-	25.6		g
Case Style	PRM1-1				

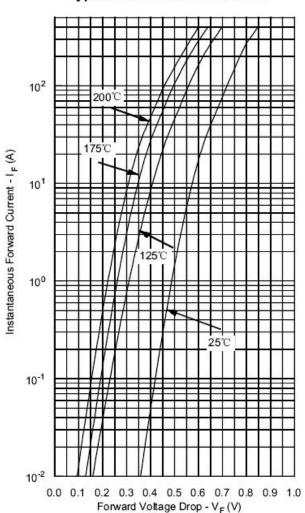




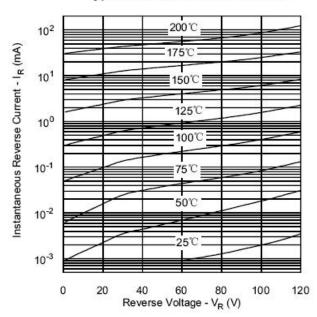


Ratings and Characteristics Curves

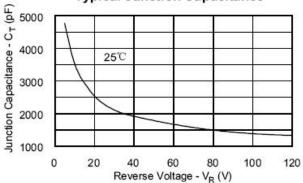
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance

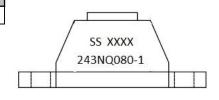


Ordering Information

Device	Package	Shipping	
243NQ SERIES	PRM1-1(Pb-Free)	27pcs/ box	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Where XXXX is YYWW

1st row SS YYWW
2nd row 243NQ080-1
SS = SS
YY = Year
WW = Week

Cautions: Molding resin

Epoxy resin UL:94V-0

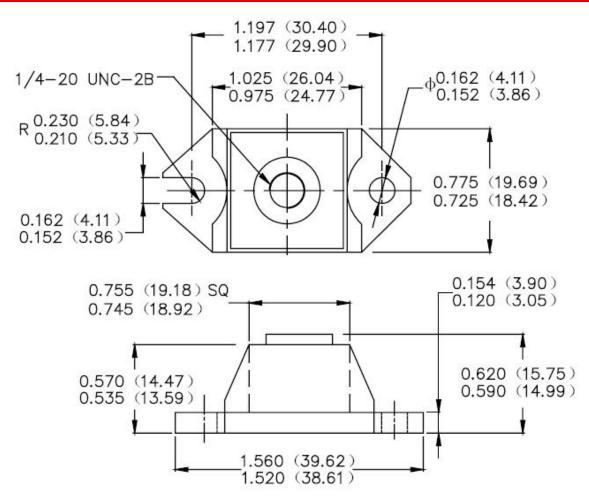
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Mechanical Dimensions PRM1-1 (Inches/Millimeters)



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